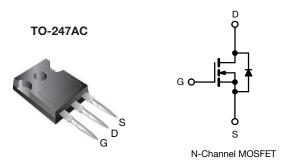
Vishay Siliconix



E Series Power MOSFET



PRODUCT SUMMA	RY	
V _{DS} (V) at T _J max.	650)
R _{DS(on)} typ. (Ω) at 25 °C	$V_{GS} = 10 V$	0.057
Q _g max. (nC)	74	
Q _{gs} (nC)	19	
Q _{gd} (nC)	15	
Configuration	Sing	le

FEATURES

- 4th generation E series technology
- Low figure-of-merit (FOM) Ron x Qg
- Low effective capacitance (Co(er))
- Reduced switching and conduction losses
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Industrial
 - Welding
 - Motor drives
 - Battery chargers
 - Solar (PV inverters)

ORDERING INFORMATION	
Package	TO-247AC
Lead (Pb)-free and halogen-free	SiHG065N60E-GE3

ABSOLUTE MAXIMUM RATINGS (T C	= 25 °C, unl	ess otherwis	se noted)		
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V _{DS}	600	v
Gate-source voltage			V _{GS}	± 30	v
Continuous drain surrent $(T_{\rm r} = 150 ^{\circ}{\rm C})$	V _{GS} at 10 V	T _C = 25 °C T _C = 100 °C	1	40	
Continuous drain current ($T_J = 150 \ ^\circ C$)	VGS at 10 V	T _C = 100 °C	ID	25	А
Pulsed drain current ^a			I _{DM}	116	
Linear derating factor				2	W/°C
Single pulse avalanche energy ^b			E _{AS}	226	mJ
Maximum power dissipation			P _D	250	W
Operating junction and storage temperature range			T _J , T _{stg}	-55 to +150	°C
Drain-source voltage slope $T_J = 125 \text{ °C}$		-l) / /-lt	100		
Reverse diode dV/dt ^d	•		dV/dt	50	V/ns
Soldering recommendations (peak temperature) ^c	For	10 s		260	°C

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature

b. V_{DD} = 120 V, starting T_J = 25 °C, L = 28.2 mH, R_g = 25 $\Omega,$ I_{AS} = 4 A

c. 1.6 mm from case

d. $I_{SD} \leq I_D$, di/dt = 400 A/µs, starting T_J = 25 °C

1



COMPLIANT

HALOGEN

FREE



Gate-source leakage

Zero gate voltage drain current

Forward transconductance

Drain-source on-state resistance

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PARAMETER	SYMBOL	TYP.	MAX.			UNIT	
Maximum junction-to-ambient	R _{thJA}	-	40			°C/W	
Maximum junction-to-case (drain)	R _{thJC}	-	0.5			C/ W	
SPECIFICATIONS (T _J = 25 °C		,					1
SPECIFICATIONS (T _J = 25 °C PARAMETER	, unless otherwis SYMBOL	se noted) TEST CONDITI	ONS	MIN.	TYP.	MAX.	UNIT
		,	ONS	MIN.	TYP.	MAX.	UNIT
PARAMETER		,		MIN. 600	TYP.	MAX.	UNIT
PARAMETER Static	SYMBOL	TEST CONDITI	50 μA		 	- -	1

V_{GS} = 10 V

I_{GSS}

IDSS

R_{DS(on)}

g_{fs}

 $V_{GS} = \pm 20 V$

 $V_{GS} = \pm 30 V$

 $V_{DS} = 600 \text{ V}, V_{GS} = 0 \text{ V}$

 V_{DS} = 480 V, V_{GS} = 0 V, T_J = 125 $^\circ C$

 $V_{DS} = 20 \text{ V}, \text{ I}_{D} = 16 \text{ A}$

 $I_{D} = 16 \text{ A}$

-

_

-

-

_

-

-

_

-

-

0.057

12

± 100

± 1

1

10

0.065

-

nA

μΑ

μΑ

Ω

S

Input capacitance	Ciss		V _{GS} = 0 V,	-	2700	-	
Output capacitance	Coss	,	V _{DS} = 100 V,	-	102	-	
Reverse transfer capacitance	C _{rss}		f = 1 MHz	-	5	-	
Effective output capacitance, energy related ^a	C _{o(er)}		/ to 480 V, V _{GS} = 0 V	-	93	-	pF
Effective output capacitance, time related ^b	C _{o(tr)}	v _{DS} = 0	$v_{10} 460 v, v_{GS} = 0 v$	-	593	-	
Total gate charge	Qg			-	49	74	
Gate-source charge	Q_gs	V _{GS} = 10 V	$I_D = 16 \text{ A}, V_{DS} = 480 \text{ V}$	-	19	-	nC
Gate-drain charge	Q _{gd}			-	15	-	
Turn-on delay time	t _{d(on)}			-	28	56	
Rise time	t _r	V _{DD} =	= 480 V, I _D = 16 A,	-	46	92	20
Turn-off delay time	t _{d(off)}	V _{GS} =	= 10 V, R _g = 9.1 Ω	-	54	108	ns
Fall time	t _f			-	13	26	
Gate input resistance	Rg	f = 1	MHz, open drain	0.3	0.7	1.4	Ω
Drain-Source Body Diode Characteristics	5						
Continuous source-drain diode current	I _S	MOSFET sym showing the	bol	-	-	40	А
Pulsed diode forward current	I _{SM}	integral revers p - n junction		-	-	116	~
Diode forward voltage	V _{SD}	T _J = 25 °C	C, I _S = 16 A, V _{GS} = 0 V	-	-	1.2	V
Reverse recovery time	t _{rr}			-	382	764	ns
Reverse recovery charge	Q _{rr}		5 °C, I _F = I _S = 16 A, 00 A/us. V _B = 400 V	-	7.1	14.2	μC
Reverse recovery current	I _{BBM}		5577µ6, V _R - 400 V	-	34	-	Α

a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}

b. Coss(tr) is a fixed capacitance that gives the same charging time as Coss while VDS is rising from 0 % to 80 % VDSS

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

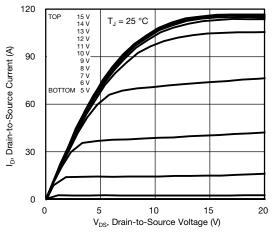
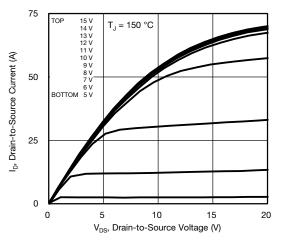


Fig. 1 - Typical Output Characteristics





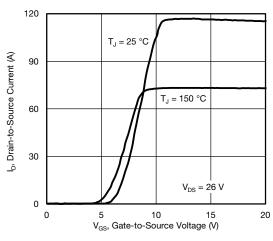


Fig. 3 - Typical Transfer Characteristics

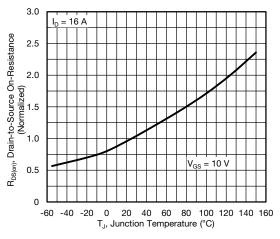


Fig. 4 - Normalized On-Resistance vs. Temperature

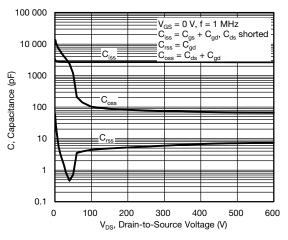


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

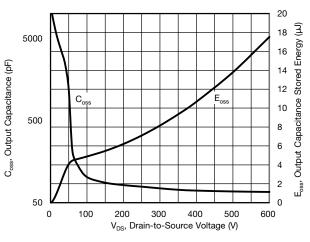


Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}

S20-0338-Rev. C, 11-May-2020

3 For technical questions, contact: <u>hvm@vishay.com</u> Document Number: 92036

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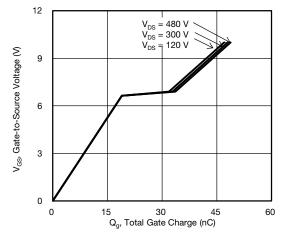


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

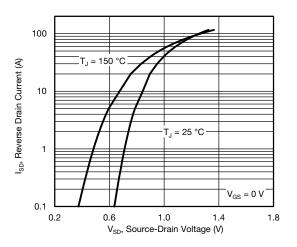
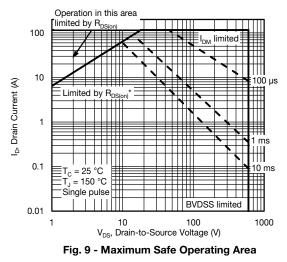


Fig. 8 - Typical Source-Drain Diode Forward Voltage



Note

a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

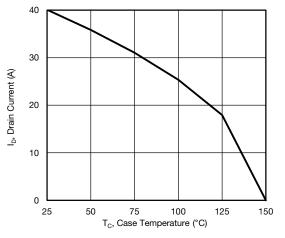


Fig. 10 - Maximum Drain Current vs. Case Temperature

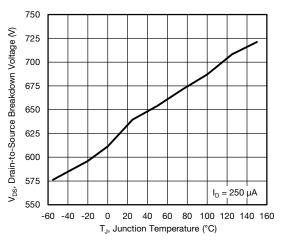


Fig. 11 - Temperature vs. Drain-to-Source Voltage

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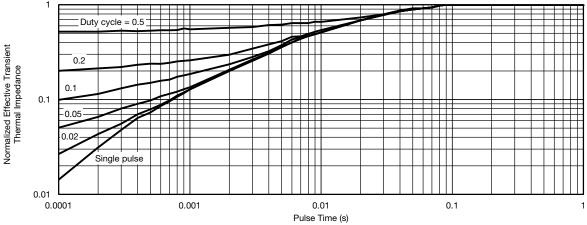


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

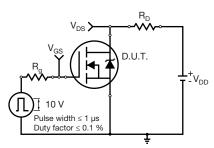


Fig. 13 - Switching Time Test Circuit

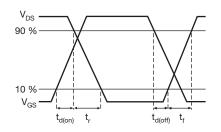


Fig. 14 - Switching Time Waveforms

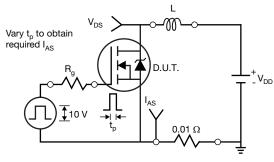


Fig. 15 - Unclamped Inductive Test Circuit

Fig. 16 - Unclamped Inductive Waveforms

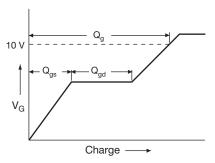


Fig. 17 - Basic Gate Charge Waveform

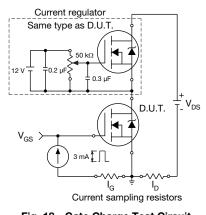
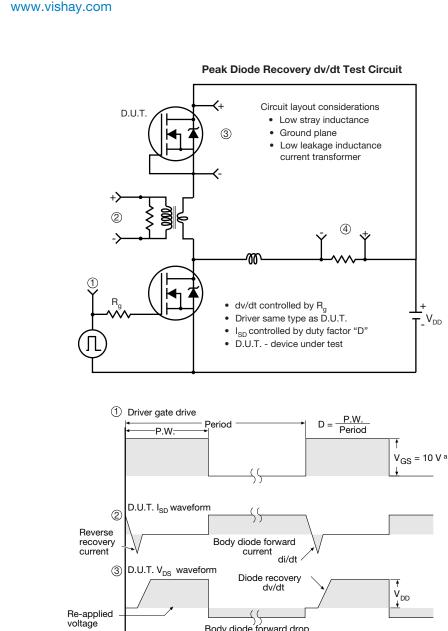


Fig. 18 - Gate Charge Test Circuit

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Body diode forward drop

Fig. 19 - For N-Channel

Ripple ≤ 5 %

a. $V_{GS} = 5 V$ for logic level devices

ŧ I_{SD}

Inductor current

4

Note

SHA

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TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9





Section C--C, D--D, E--E

	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
А	4.83	5.21	
A1	2.29	2.55	
A2	1.50	2.49	
b	1.12	1.33	
b1	1.12	1.28	
b2	1.91	2.39	6
b3	1.91	2.34	
b4	2.87	3.22	6, 8
b5	2.87	3.18	
С	0.55	0.69	6
c1	0.55	0.65	
D	20.40	20.70	4

	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
D1	16.25	16.85	5
D2	0.56	0.76	
E	15.50	15.87	4
E1	13.46	14.16	5
E2	4.52	5.49	3
е	5.44	BSC	
L	14.90	15.40	
L1	3.96	4.16	6
ØP	3.56	3.65	7
Ø P1	7.19) ref.	
Q	5.31	5.69	
S	5.54	5.74	

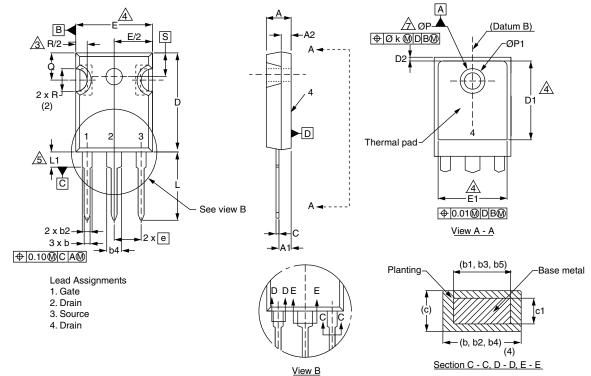
Notes

- ⁽¹⁾ Package reference: JEDEC[®] TO247, variation AC
- (2) All dimensions are in mm
- ⁽³⁾ Slot required, notch may be rounded
- ⁽⁴⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁵⁾ Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- (7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition

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VERSION 2: FACILITY CODE = Y



	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
А	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
с	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

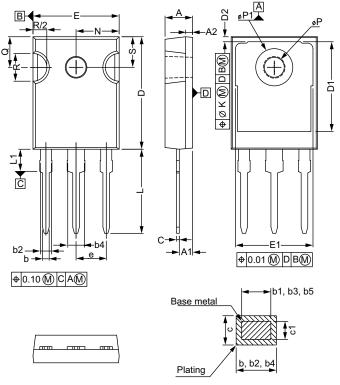
	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.2	254	
L	14.20	16.25	
L1	3.71	4.29	
ØΡ	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51	BSC	

Notes

- ⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994
- ⁽²⁾ Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁴⁾ Thermal pad contour optional with dimensions D1 and E1
- ⁽⁵⁾ Lead finish uncontrolled in L1
- ⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- ⁽⁷⁾ Outline conforms to JEDEC outline TO-247 with exception of dimension c



VERSION 3: FACILITY CODE = N



	MILLIN	IETERS		MILLIN	IETERS
DIM.	MIN.	MAX.	DIM.	MIN.	MAX.
А	4.65	5.31	D2	0.51	1.35
A1	2.21	2.59	E	15.29	15.87
A2	1.17	1.37	E1	13.46	-
b	0.99	1.40	е	5.46	BSC
b1	0.99	1.35	k	0.:	254
b2	1.65	2.39	L	14.20	16.10
b3	1.65	2.34	L1	3.71	4.29
b4	2.59	3.43	N	7.62	BSC
b5	2.59	3.38	Р	3.56	3.66
С	0.38	0.89	P1	-	7.39
c1	0.38	0.84	Q	5.31	5.69
D	19.71	20.70	R	4.52	5.49
D1	13.08	-	S	5.51	BSC

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

⁽²⁾ Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁴⁾ Thermal pad contour optional with dimensions D1 and E1

⁽⁵⁾ Lead finish uncontrolled in L1

⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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